



FDMS86310

N-Channel PowerTrench[®] MOSFET

80 V, 50 A, 4.8 mΩ

Features

- Max $r_{DS(on)}$ = 4.8 mΩ at $V_{GS} = 10$ V, $I_D = 17$ A
- Max $r_{DS(on)}$ = 6.7 mΩ at $V_{GS} = 8$ V, $I_D = 14$ A
- Advanced Package and Silicon combination for low $r_{DS(on)}$ and high efficiency
- Next generation enhanced body diode technology, engineered for soft recovery
- MSL1 robust package design
- 100% UIL tested
- RoHS Compliant

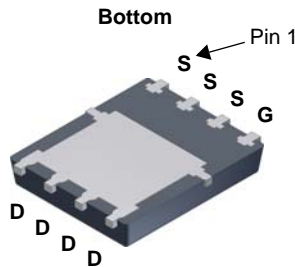
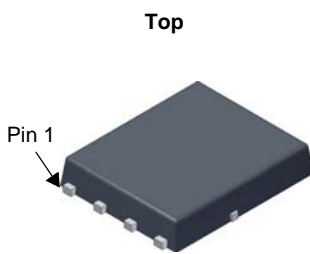


General Description

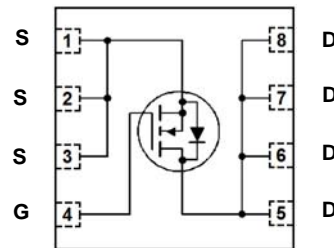
This N-Channel MOSFET has been designed specifically to improve the overall efficiency and to minimize switch node ringing of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $r_{DS(on)}$, fast switching speed and body diode reverse recovery performance.

Applications

- Primary Switch
- Synchronous Rectifier
- Motor Switch



Power 56



MOSFET Maximum Ratings $T_A = 25$ °C unless otherwise noted

Symbol	Parameter	Rated	Units
V_{DS}	Drain to Source Voltage	80	V
V_{GS}	Gate to Source Voltage	±20	V
I_D	Drain Current -Continuous (Package limited) $T_C = 25$ °C	50	A
	-Continuous (Silicon limited) $T_C = 25$ °C	105	
	-Continuous $T_A = 25$ °C (Note 1a)	17	
	-Pulsed	100	
E_{AS}	Single Pulse Avalanche Energy (Note 3)	183	mJ
P_D	Power Dissipation $T_C = 25$ °C	96	W
	Power Dissipation $T_A = 25$ °C (Note 1a)	2.5	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	50	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS86310	FDMS86310	Power 56	13 "	12 mm	3000 units

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\ \mu\text{A}, V_{GS} = 0\ \text{V}$	80			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, referenced to 25°C		45		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 64\ \text{V}, V_{GS} = 0\ \text{V}$			1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\ \text{V}, V_{DS} = 0\ \text{V}$			± 100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\ \mu\text{A}$	2.4	3.3	4.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, referenced to 25°C		-11		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\ \text{V}, I_D = 17\ \text{A}$		3.8	4.8	m Ω
		$V_{GS} = 8\ \text{V}, I_D = 14\ \text{A}$		4.5	6.7	
		$V_{GS} = 10\ \text{V}, I_D = 17\ \text{A}, T_J = 125^\circ\text{C}$		5.7	7.2	
g_{FS}	Forward Transconductance	$V_{DS} = 10\ \text{V}, I_D = 17\ \text{A}$		49		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 40\ \text{V}, V_{GS} = 0\ \text{V}, f = 1\ \text{MHz}$		4730	6290	pF
C_{oss}	Output Capacitance			693	925	pF
C_{rss}	Reverse Transfer Capacitance			19	45	pF
R_g	Gate Resistance			1.3		Ω

Switching Characteristics

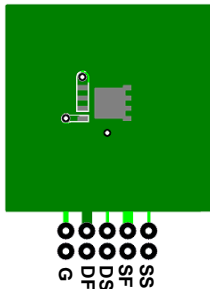
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 40\ \text{V}, I_D = 17\ \text{A}, V_{GS} = 10\ \text{V}, R_{GEN} = 6\ \Omega$		28	45	ns	
t_r	Rise Time			23	37	ns	
$t_{d(off)}$	Turn-Off Delay Time			35	56	ns	
t_f	Fall Time			9	18	ns	
Q_g	Total Gate Charge		$V_{GS} = 0\ \text{V to } 10\ \text{V}$	$V_{DD} = 40\ \text{V}, I_D = 17\ \text{A}$	66	95	nC
Q_g	Total Gate Charge		$V_{GS} = 0\ \text{V to } 8\ \text{V}$		55	78	nC
Q_{gs}	Gate to Source Charge		24			nC	
Q_{gd}	Gate to Drain "Miller" Charge		14			nC	

Drain-Source Diode Characteristics

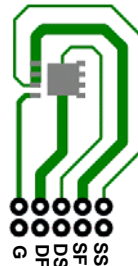
V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\ \text{V}, I_S = 2.1\ \text{A}$ (Note 2)		0.72	1.2	V
		$V_{GS} = 0\ \text{V}, I_S = 17\ \text{A}$ (Note 2)		0.81	1.3	
t_{rr}	Reverse Recovery Time	$I_F = 17\ \text{A}, di/dt = 100\ \text{A}/\mu\text{s}$		51	80	ns
Q_{rr}	Reverse Recovery Charge			41	65	nC
t_{rr}	Reverse Recovery Time	$I_F = 17\ \text{A}, di/dt = 300\ \text{A}/\mu\text{s}$		43	69	ns
Q_{rr}	Reverse Recovery Charge			87	140	nC

Notes:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 50 $^\circ\text{C}/\text{W}$ when mounted on a 1 in² pad of 2 oz copper



b) 125 $^\circ\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0%.

3. Starting $T_J = 25^\circ\text{C}$, $L = 0.3\ \text{mH}$, $I_{AS} = 35\ \text{A}$, $V_{DD} = 72\ \text{V}$, $V_{GS} = 10\ \text{V}$.

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

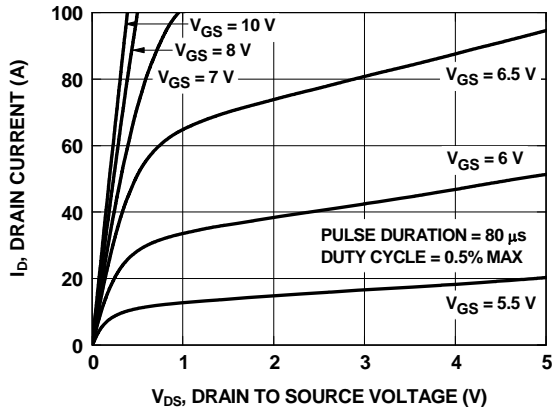


Figure 1. On-Region Characteristics

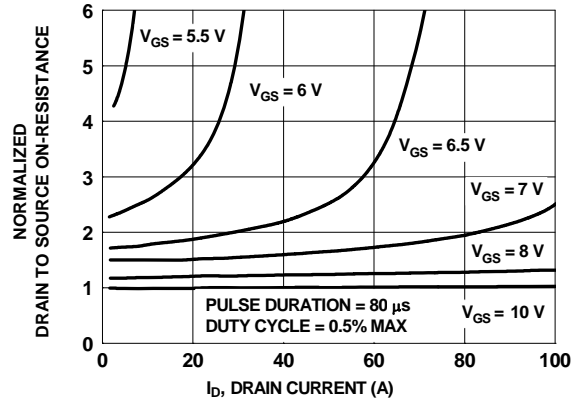


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

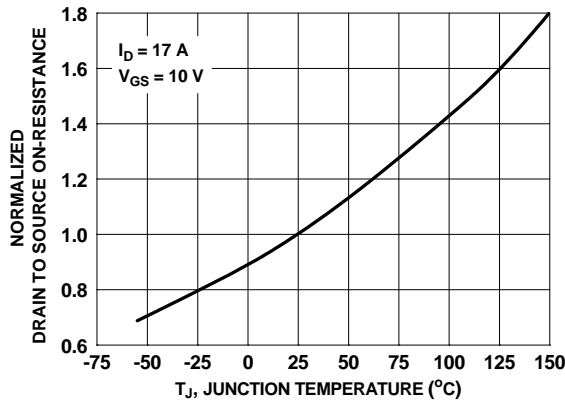


Figure 3. Normalized On-Resistance vs Junction Temperature

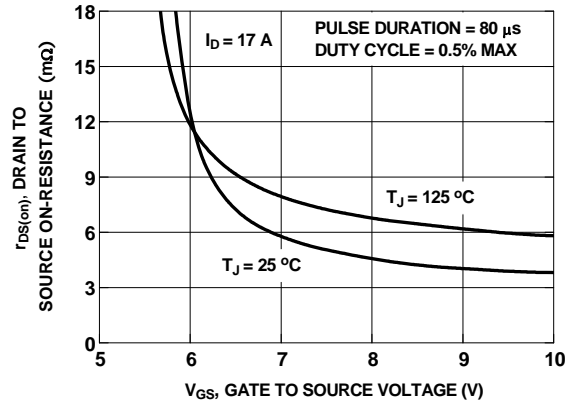


Figure 4. On-Resistance vs Gate to Source Voltage

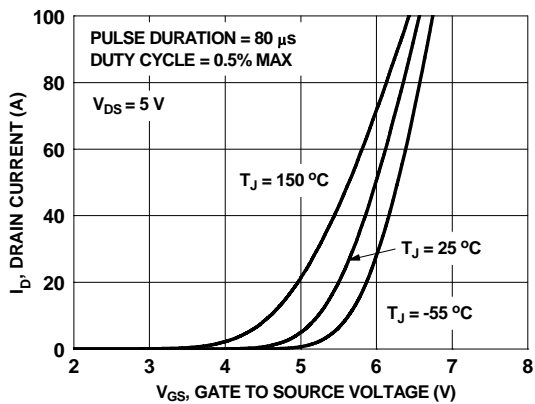


Figure 5. Transfer Characteristics

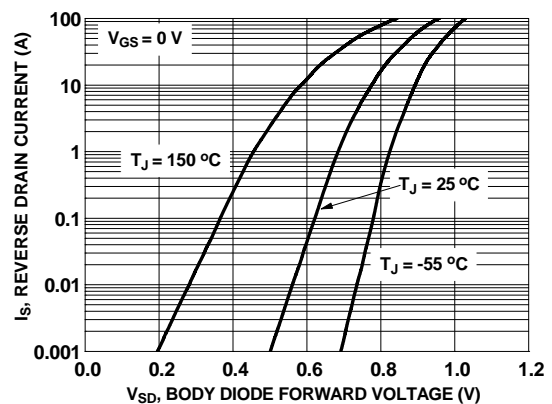


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

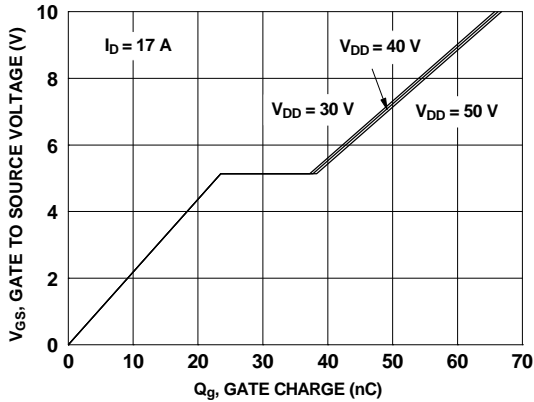


Figure 7. Gate Charge Characteristics

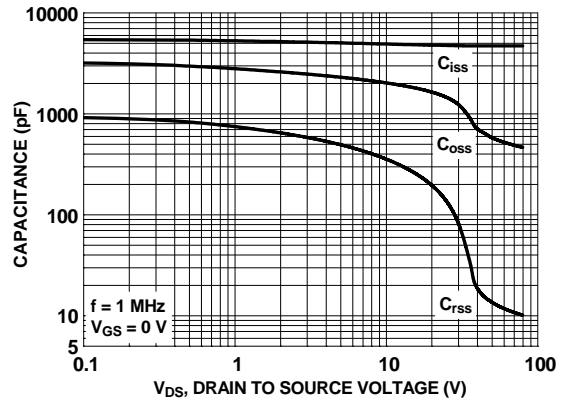


Figure 8. Capacitance vs Drain to Source Voltage

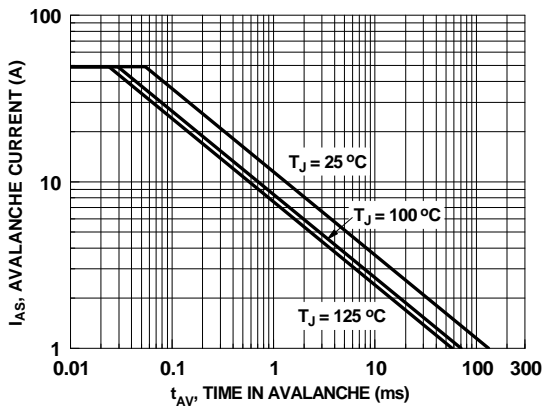


Figure 9. Unclamped Inductive Switching Capability

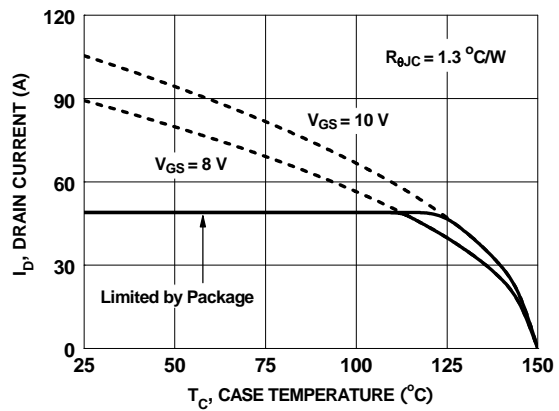


Figure 10. Maximum Continuous Drain Current vs Case Temperature

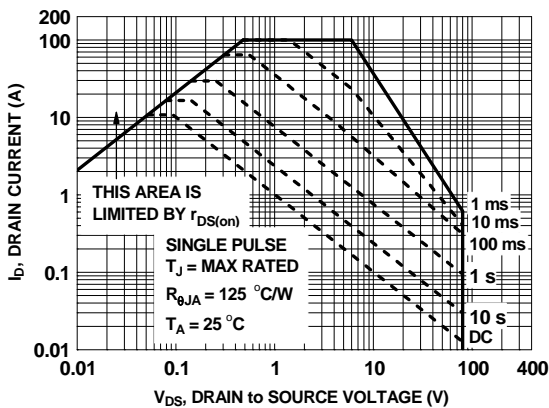


Figure 11. Forward Bias Safe Operating Area

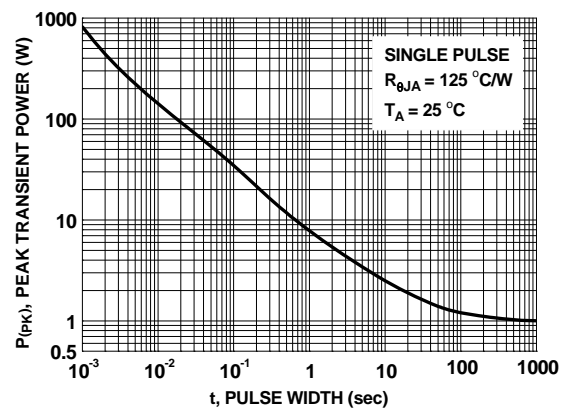


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

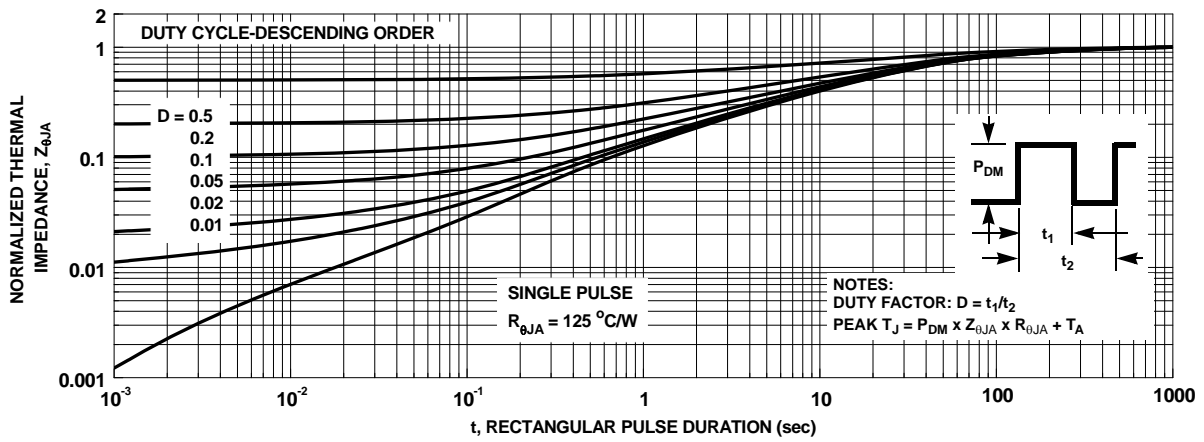
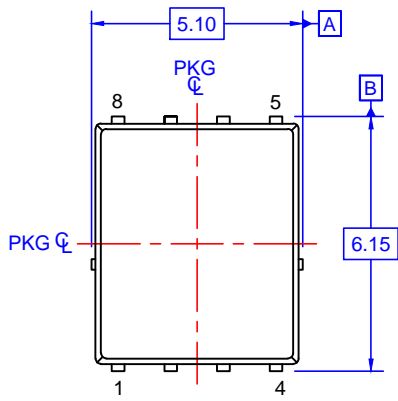
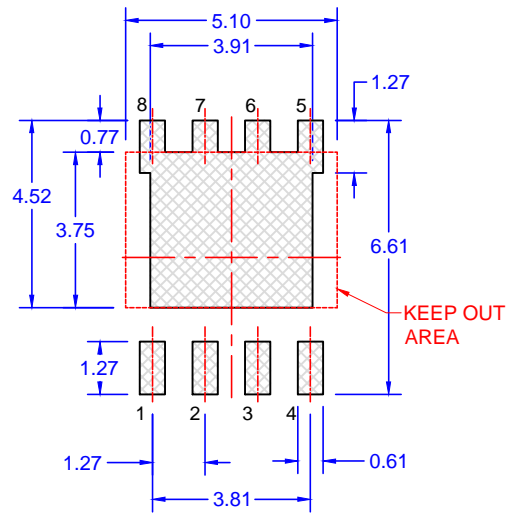
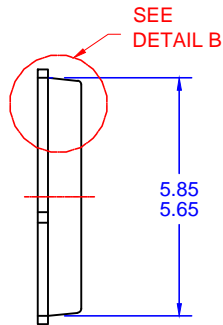


Figure 13. Junction-to-Ambient Transient Thermal Response Curve

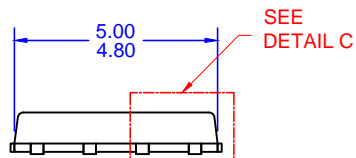
PQFN8 5X6, 1.27P
CASE 483AE
ISSUE A



TOP VIEW

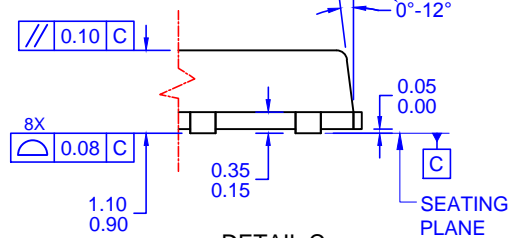


LAND PATTERN RECOMMENDATION

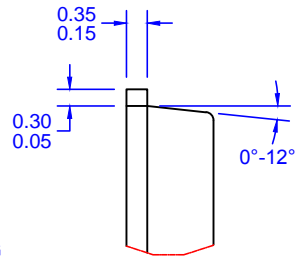


SIDE VIEW

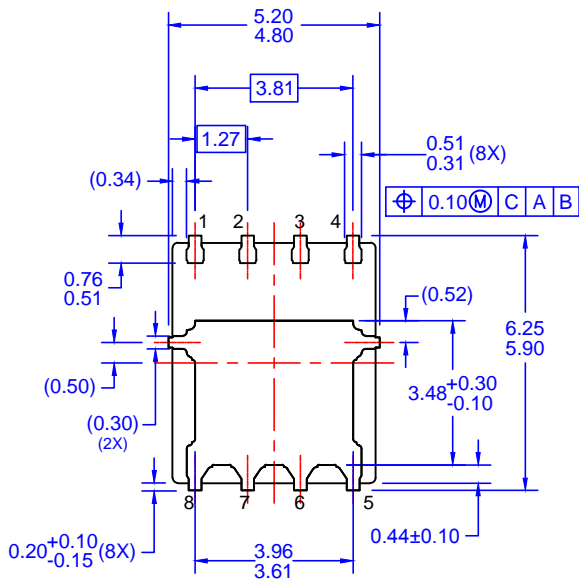
OPTIONAL DRAFT ANGLE MAY APPEAR ON FOUR SIDES OF THE PACKAGE



DETAIL C
SCALE: 2:1



DETAIL B
SCALE: 2:1



BOTTOM VIEW

NOTES: UNLESS OTHERWISE SPECIFIED

- A. PACKAGE STANDARD REFERENCE: JEDEC MO-240, ISSUE A, VAR. AA.
- B. DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
- E. IT IS RECOMMENDED TO HAVE NO TRACES OR VIAS WITHIN THE KEEP OUT AREA.

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